

## 2N6426



## **NPN Darlington Transistor**

This device is designed for applications requiring extremely high current gain at currents to 1.0 A. Sourced from Process 05. See MPSA14 for characteristics.

## **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{CEO}$	Collector-Emitter Voltage	40	V	
V <sub>CBO</sub>	Collector-Base Voltage	40	V	
V <sub>EBO</sub>	Emitter-Base Voltage	12	V	
Ic	Collector Current - Continuous 1		A	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## **Thermal Characteristics**

TA = 25°C unless otherwise noted

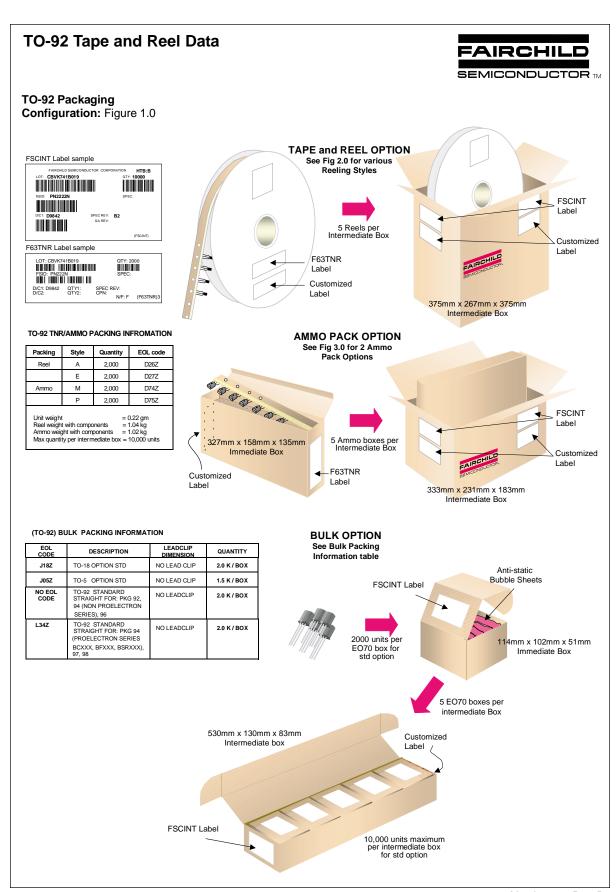
Symbol	Characteristic	Max	Units
		2N6426	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

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## NPN Darlington Transistor (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	40		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100  \mu A, I_E = 0$	40		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	12		V
СВО	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		50	nA
CEO	Collector Cutoff Current	$V_{CE} = 25 \text{ V}, I_{B} = 0$		1.0	μΑ
ЕВО	Emitter Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$		50	nA
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$V_{CE} = 5.0 \text{ V}, I_C = 500 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 0.5 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 0.5 \text{ mA}$	20,000	200,000 1.2 1.5	V
VCE(Sat)	Composed Emiliar Catalian Contage				
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 0.5 \text{ mA}$		2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 50 \text{ mA}, V_{CE} = 5.0 \text{ V}$		1.75	V
SMALL S	SIGNAL CHARACTERISTICS Output Capacitance	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		7.0	pF
C <sub>ib</sub>	Input Capacitance	$V_{EB} = 1.0 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz}$		15	pF
h <sub>fe</sub>	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0  kHz	20,000		•
h <sub>ie</sub>	Input Impedance	$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$	100	2,000	kΩ
h <sub>oe</sub>	Output Admittance	f = 1.0 kHz		1,000	μmho
NF	Noise Figure	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $R_S = 100 \text{ k}\Omega,$ $f = 10 \text{ kHz to } 15.7 \text{ kHz}$		10	dB

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

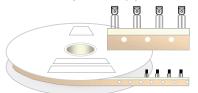


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## TO-92 Tape and Reel Data, continued

## **TO-92 Reeling Style Configuration:** Figure 2.0

## Machine Option "A" (H)

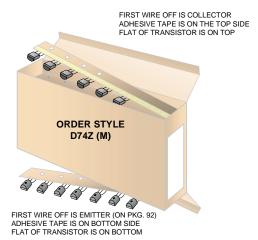


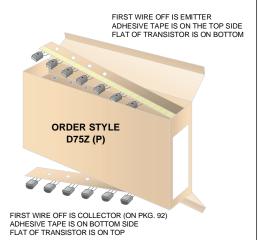
Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

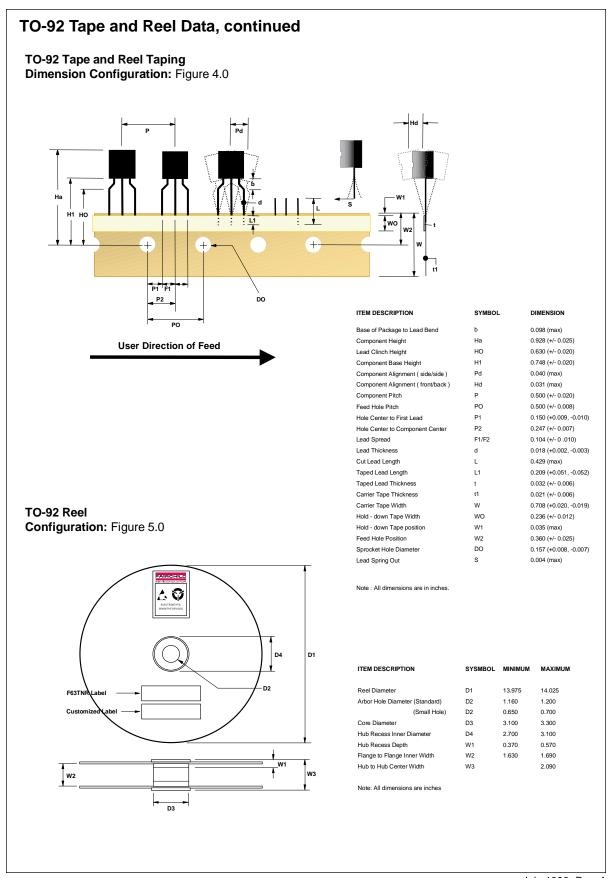
Style "E", D27Z, D71Z (s/h)

## **TO-92 Radial Ammo Packaging Configuration:** Figure 3.0





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## **TO-92 Package Dimensions** FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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0.095 0.084 2.13

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